

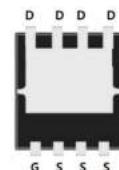


Features

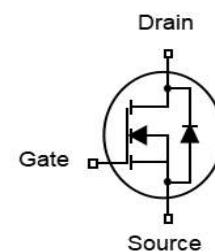
- N-Channel
- Very low on-resistance $R_{DS(on)}$
- Low Crss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 100% EAS Tested

V_{DS}	30	V
$R_{DS(on),TYP}@ V_{GS}=10\text{ V}$	6.2	$\text{m}\Omega$
$R_{DS(on),TYP}@ V_{GS}=4.5\text{ V}$	10	$\text{m}\Omega$
I_D	30	A

DFN3x3



Part ID	Package Type	Marking	Packing
ZT060N03Q	DFN3x3	ZT060N03Q	5000pcs/Reel



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	± 20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	30	V
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c = 25^\circ\text{C}$	A
Mounted on Large Heat Sink			
I_D	Drain Current-Continuous	$T_c = 25^\circ\text{C}$	A
		$T_c = 100^\circ\text{C}$	A
P_D	Maximum Power Dissipation	42	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3.6	$^\circ\text{C}/\text{W}$
Drain-Source Avalanche Ratings			
EAS	Avalanche Energy, Single Pulsed (Note 2)	70	mJ



Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ $T_J=25^\circ\text{C}$ (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	--	--	V
Idss	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$	--	--	1	μA
IGSS	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$	--	--	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	1.7	2.2	V
RDS(on)	Drain-Source On-State Resistance	$V_{GS}=10\text{V}, I_D=15\text{A}$	--	6.2	8.2	$\text{m}\Omega$
RDS(on)	Drain-Source On-State Resistance	$V_{GS}=4.5\text{V}, I_D=15\text{A}$	--	10.0	13.5	$\text{m}\Omega$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

Ciss	Input Capacitance	$V_{DS}=15\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	--	1060	--	pF
Coss	Output Capacitance		--	122	--	pF
Crss	Reverse Transfer Capacitance		--	102	--	pF
Rg	Gate Resistance	f=1MHz	--	3	--	Ω
Qg	Total Gate Charge	$V_{DS}=15\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$	--	21	--	nC
Qgs	Gate-SourceCharge		--	3	--	nC
Qgd	Gate-DrainCharge		--	5	--	nC

Switching Characteristics (Note 3)

Td(on)	Turn-on Delay Time	$V_{DS}=15\text{V}, I_D = 30\text{A}, R_L = 1.6\Omega, V_{GS}=10\text{V}$	--	4	--	ns
Tr	Turn-on Rise Time		--	2	--	ns
Td(off)	Turn-Off Delay Time		--	13	--	ns
Tf	Turn-Off Fall Time		--	7	--	ns

Source-Drain Diode Characteristics@ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

Is	Diode Forward Current	$I_{SD}=10\text{A}, V_{GS}=0\text{V}$	--	--	30	A
ISM	Maximum Pulsed Drain-Source Diode Forward Current		--	--	120	A
VSD	Forward on voltage	I _{SD} =10A, V _{GS} =0V	--	--	1.2	V

Notes:

- Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- EAS condition: $T_J=25^\circ\text{C}, V_{DD}=20\text{V}, V_G=10\text{V}, L=0.5\text{mH}$.
- Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

N- Channel Typical Characteristics

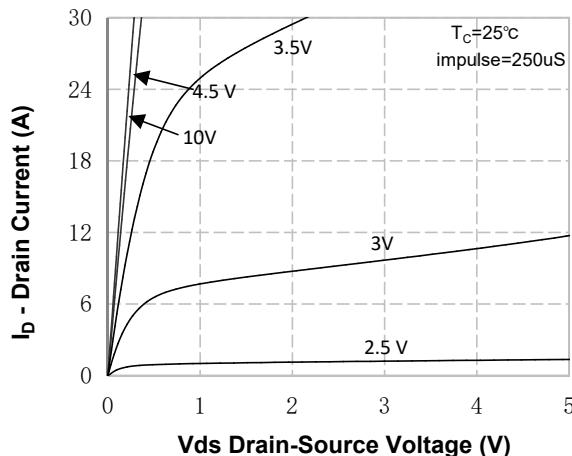


Figure 1. On-Region Characteristics

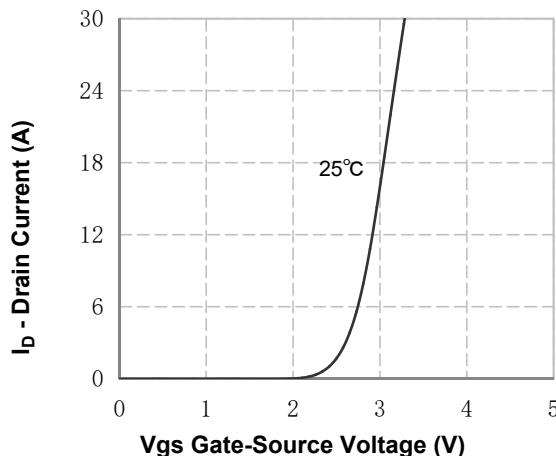


Figure 4. Transfer Characteristics

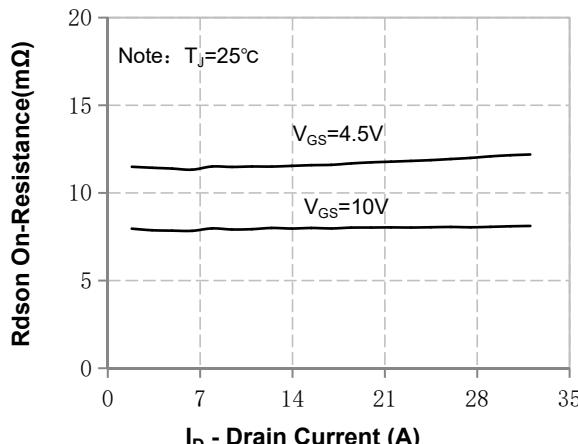


Figure 2. On-Resistance Variation vs Drain Current and Gate Voltage

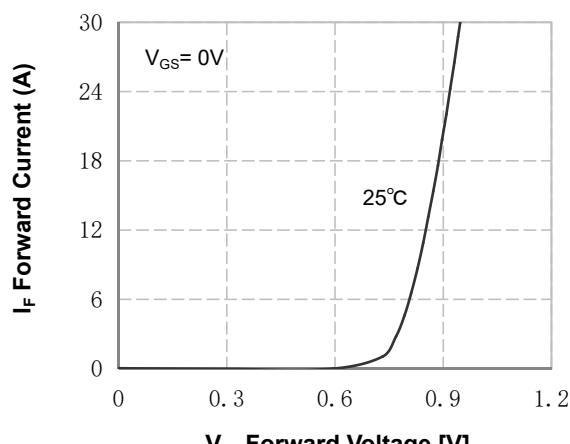


Figure 5. Body Diode Forward Voltage Variation vs Source Current

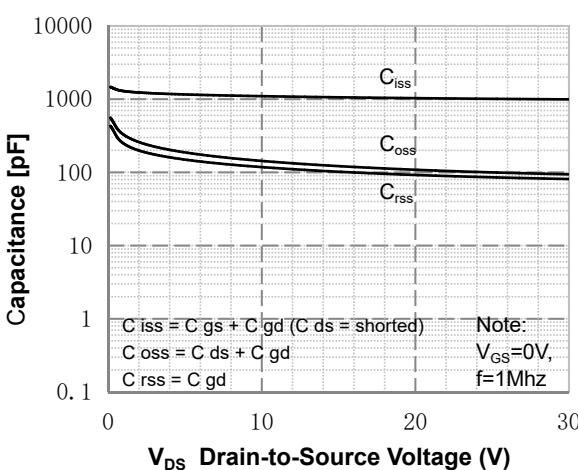


Figure 3. Capacitance Characteristics

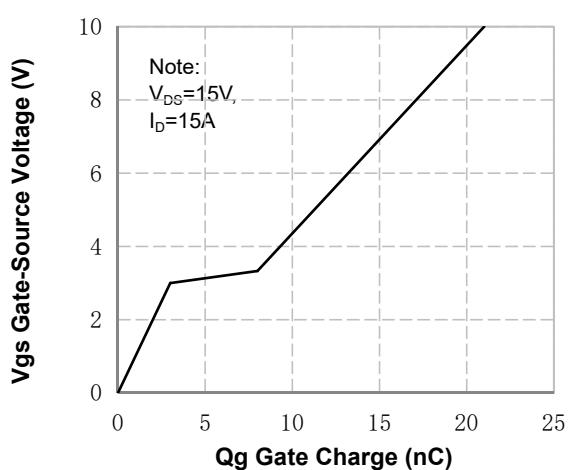


Figure 6. Gate Charge Characteristics

N- Channel Typical Characteristics (Continued)

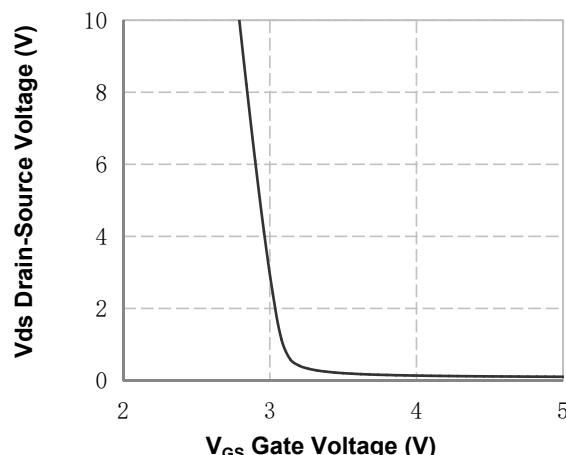


Figure 7. V_{ds} Drain-Source Voltage vs Gate Voltage

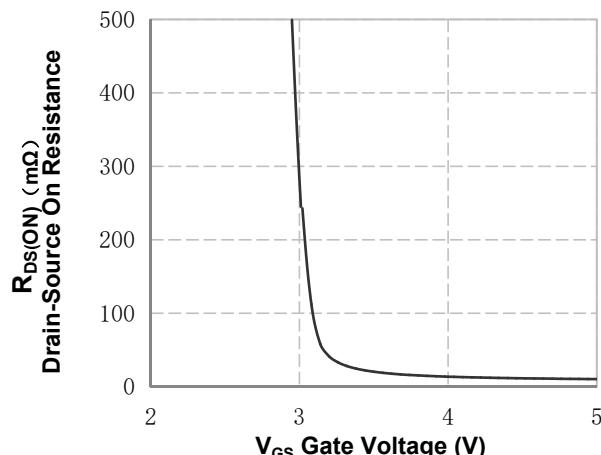


Figure 9. On-Resistance vs Gate Voltage

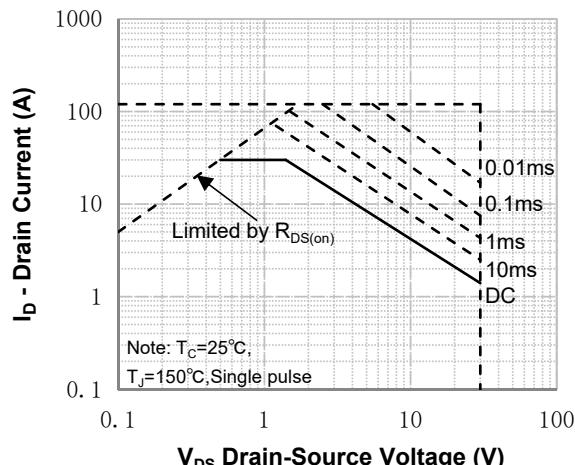


Figure 8. Maximum Safe Operating Area

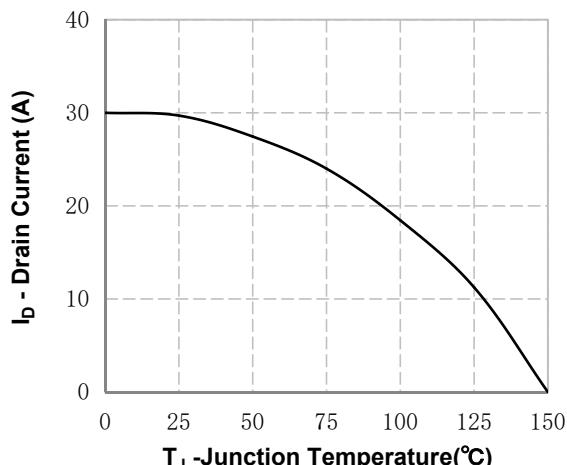


Figure 10. Maximum Continuous Drain Current vs Temperature

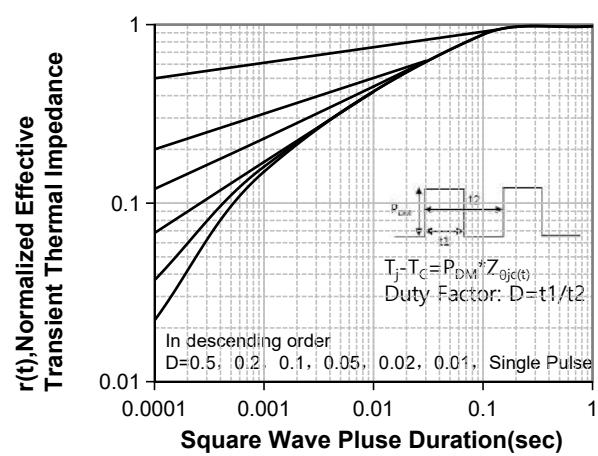
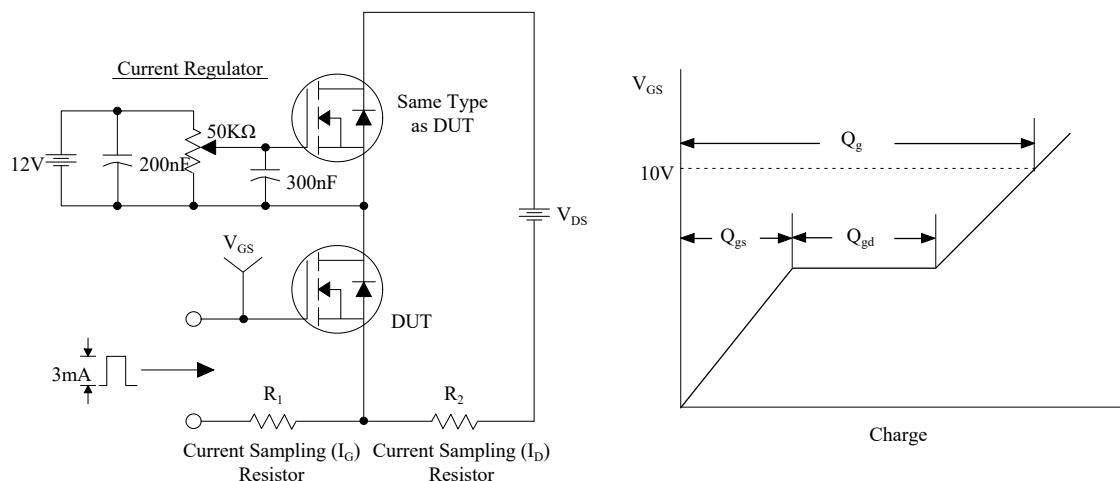
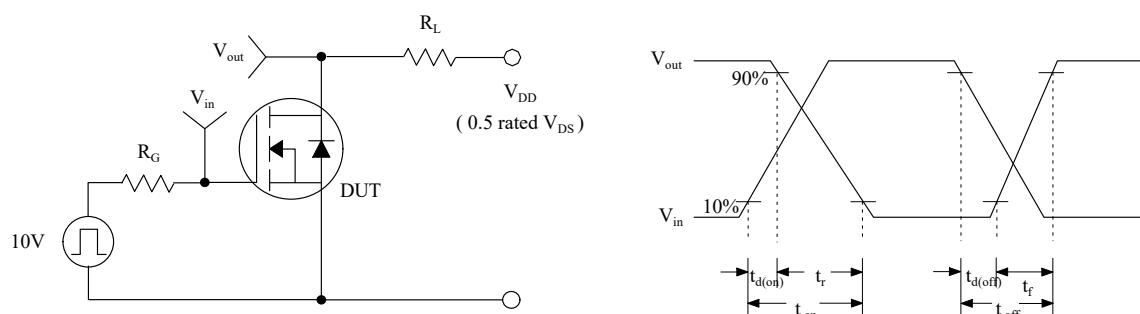


Figure 11. Transient Thermal Response Curve

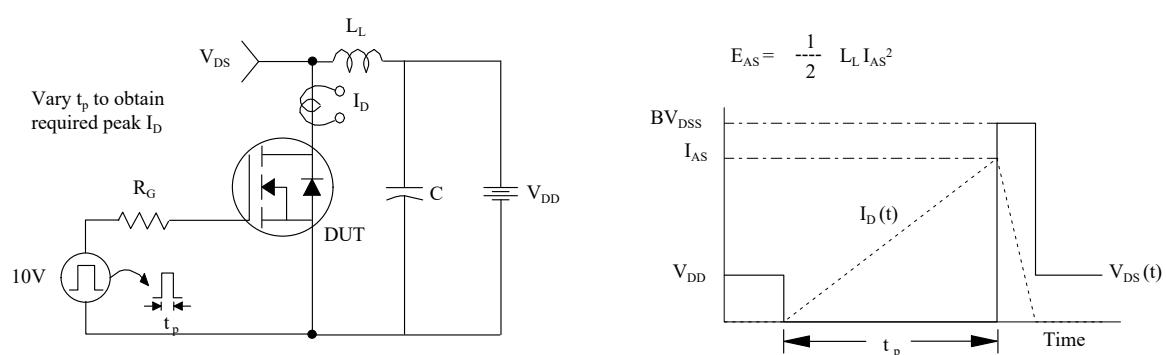
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

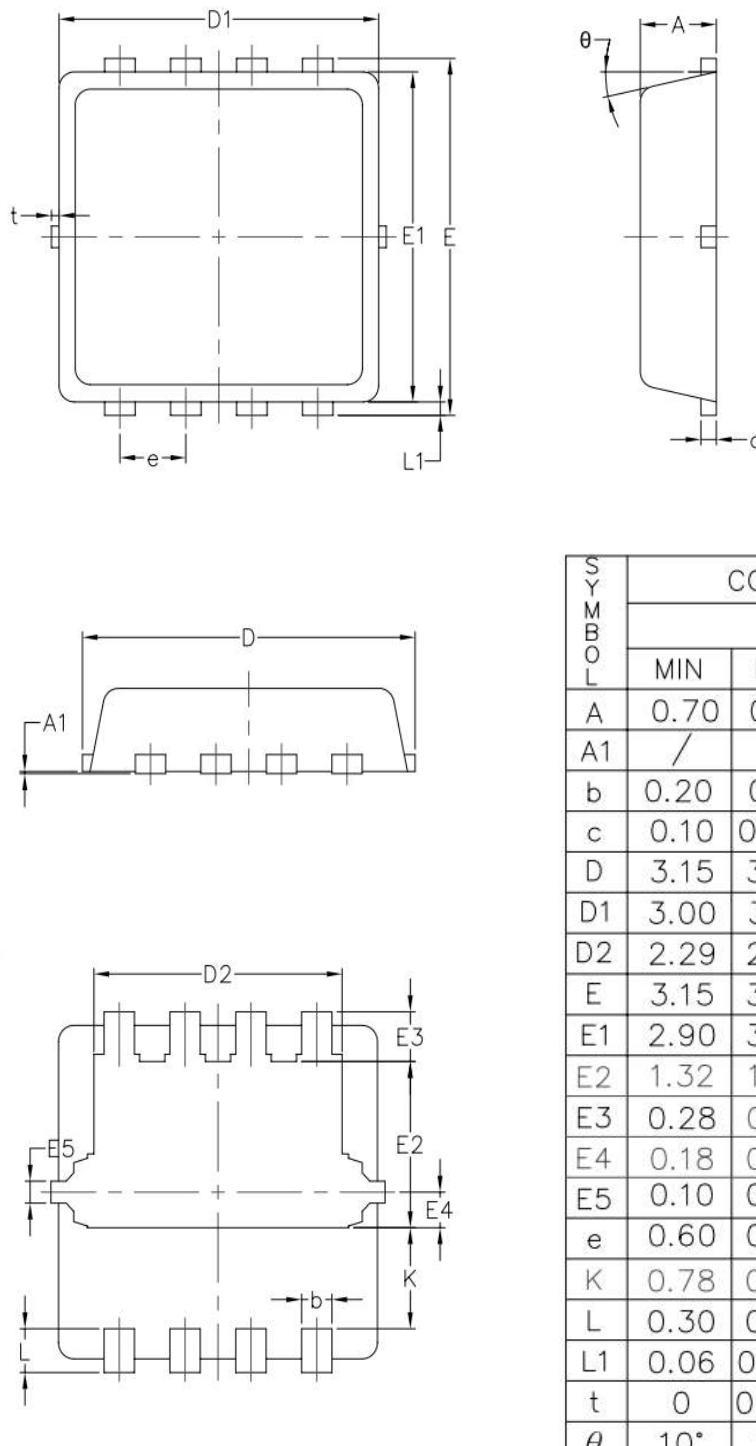


Unclamped Inductive Switching Test Circuit & Waveforms





DFN3x3-8L Package Information



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.32	1.52	1.72
E3	0.28	0.46	0.65
E4	0.18	0.33	0.48
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.78	0.93	1.13
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
θ	10°	12°	14°

Customer Service

Sales and Service:

zj@ztasemi.com